

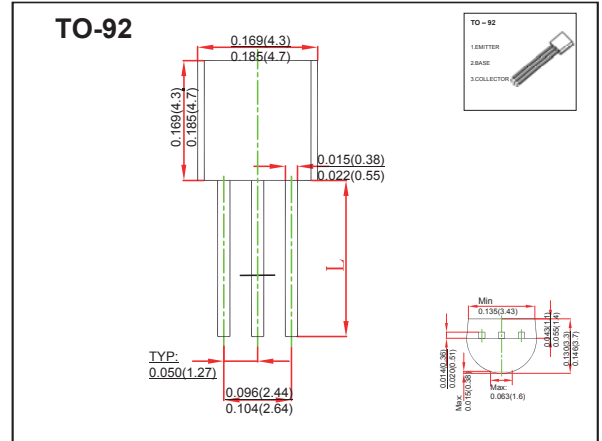
TO-92 Plastic-Encapsulate Transistors

FEATURES

- High DC Current Gain
- Complementary Pair with 2SC5344
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style: TO-92 molded plastic
- Mounting position: any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-35	V
V_{CE0}	Collector-Emitter Voltage	-30	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.8	A
P_D	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	200	°C / W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 ~ +150	°C

ORDERING INFORMATION

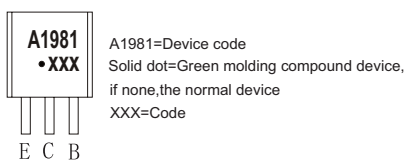
Part Number	Package	Packing Method	Pack Quantity
2SA1981	TO-92	Bulk	1000pcs/Bag
2SA1981-TA	TO-92	Tape	2000pcs/Box

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.5mA, I_E = 0$	-35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.05mA, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -35V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -1V, I_C = -100mA$	100		320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -20mA$			-0.5	V
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		19		pF
Transition frequency	f_T	$V_{CE} = -5V, I_C = -10mA$		120		MHz

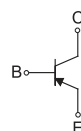
CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	100-200	160-320

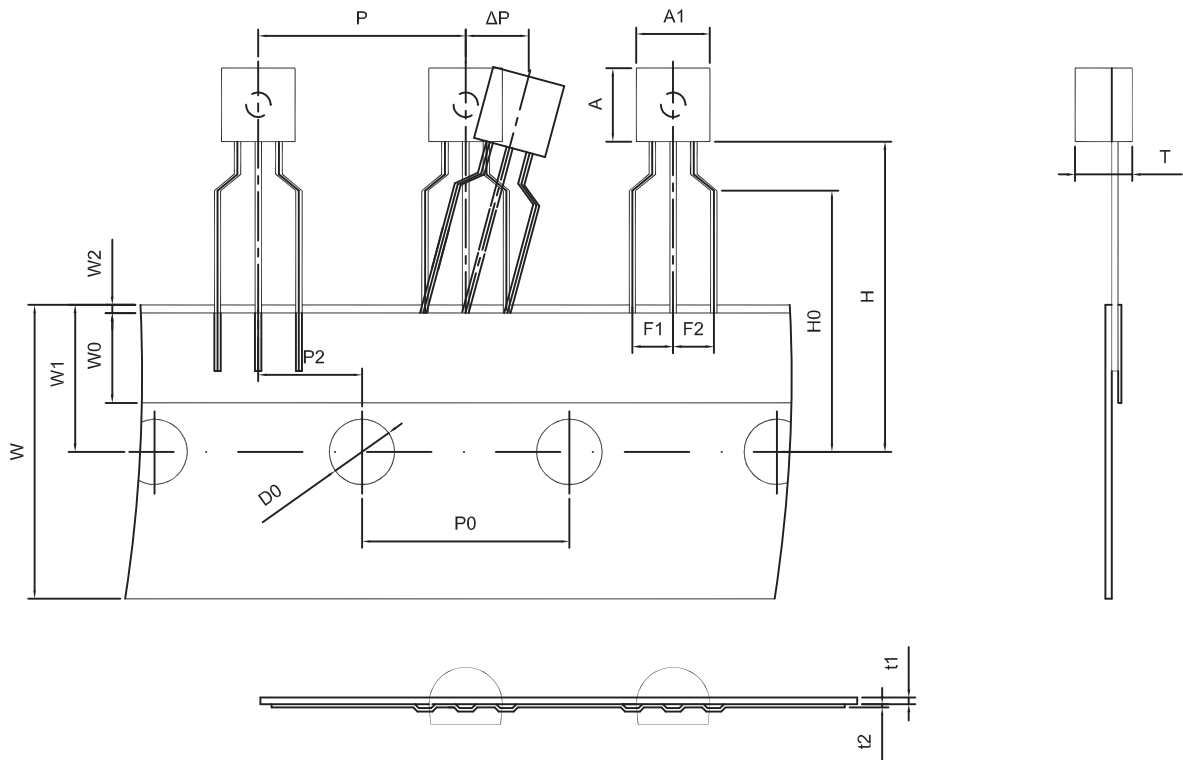
MARKING



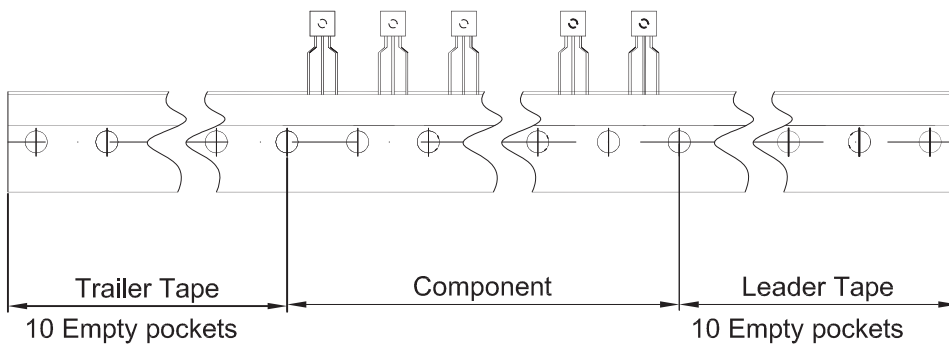
Equivalent Circuit



TO-92 PACKAGE TAPEING DIMENSION



Dimensions are in millimeter								
A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250